



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _A = +25°C
-12V	$31m\Omega$ @ $V_{GS} = -4.5V$	5.2A
-120	45mΩ @ V _{GS} =-2.5V	4.3A

Description

This new generation MOSFET is designed to minimize the on-state (R_{DS(ON)}) while maintaining superior performance, which makes the device ideal for high-efficiency powermanagement applications.

Applications

- DC-DC Converters
- **Power Management Functions**
- Analog Switch

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Data Sheet (DMP1045UQ)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish—Matte Tin Annealed Over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.009 grams (Approximate)





SOT23





Gate Protection

S

Internal Schematic

G

Top View Pin Configuration

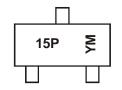
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP1045U-7	SOT23	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3).compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, see http://www.diodes.com/products/packages.html.

Marking Information



15P = Marking Code YM = Date Code Marking $Y \text{ or } \overline{Y} = Y \text{ ear (ex: } E = 2017)$ M = Month (ex: 9 = September)

Date Code Kev

Year	2010	~	20	16	2017	2018	2019	2020	20	21	2022	2023
Code	Х	7])	Е	F	G	Н		I	J	K
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	-12	V		
Gate-Source Voltage	V_{GSS}	±8	V		
Continuous Drain Current (Note 5) V _{GS} = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	4.0 3.1	А
Continuous Drain Current (Note 5) V _{GS} = -2.5V	I _D	3.3 2.6	А		
Continuous Drain Current (Note 6) V _{GS} = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	5.2 4.2	Α
Continuous Drain Current (Note 6) V _{GS} = -2.5V	I _D	4.3 3.4	Α		
Maximum Continuous Body Diode Forward Current	I _S	2	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	40	A		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	168	°C/W
Total Power Dissipation (Note 6)	P _D	1.3	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	99	°C/W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	14.8	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

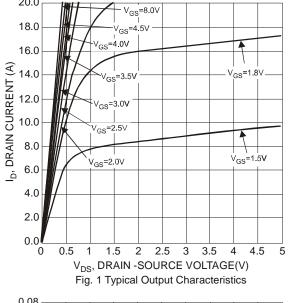
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV _{DSS}	-12	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$		
Zero Gate Voltage Drain Current (T _J = +25°C)	I _{DSS}	_	_	-1.0	μA	$V_{DS} = -12V, V_{GS} = 0V$		
Gate-Source Leakage	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V _{GS(TH)}	-0.3	-0.55	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		
			26	31		$V_{GS} = -4.5V, I_{D} = -4.0A$		
Static Drain-Source On-Resistance	R _{DS(ON)}	_	31	45	mΩ	$V_{GS} = -2.5V, I_D = -3.5A$		
			45	75		$V_{GS} = -1.8V, I_D = -2.7A$		
Forward Transfer Admittance	Y _{FS}	_	12	_	S	$V_{DS} = -5V, I_{D} = -4A$		
Diode Forward Voltage	V_{SD}	_	-0.6	_	V	$V_{GS} = 0V, I_{S} = -1A$		
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	C _{ISS}	_	1357	_	pF	10/1/1/ 01/		
Output Capacitance	Coss	_	504	_	pF	$V_{DS} = -10V, V_{GS} = 0V$ -f = 1.0MHz		
Reverse Transfer Capacitance	C _{RSS}	_	235	_	pF	1 - 1.000112		
Gate Resistnace	R _G	_	14.1	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$		
SWITCHING CHARACTERISTICS (Note 8)								
Total Gate Charge	Q_G	_	15.8	_	nC			
Gate-Source Charge	Q_{GS}	_	2.0	_	nC	$V_{GS} = -4.5V, V_{DS} = -10V, I_{D} = -4A$		
Gate-Drain Charge	Q_{GD}	_	3.9	_	nC			
Turn-On Delay Time	t _{D(ON)}	_	15.7	_	ns			
Turn-On Rise Time	t _R	_	23.3	_	ns	V _{DS} = -10V, V _{GS} = -4.5V,		
Turn-Off Delay Time	t _{D(OFF)}	_	91.2	_	ns	$R_L = 2.5\Omega$, $R_G = 3.0\Omega$		
Turn-Off Fall Time	t _F	_	106.9		ns			

Notes:

- 5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
 6. Device mounted on FR-4 substrate PCB, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.
 7 .Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to production testing.





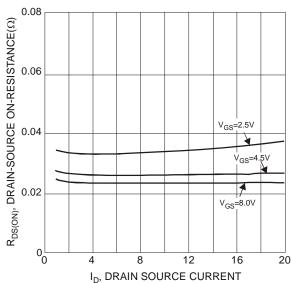
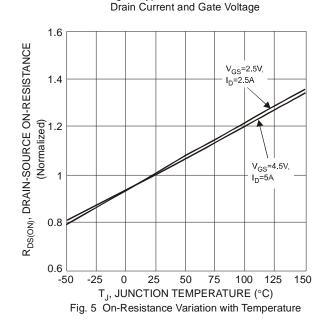
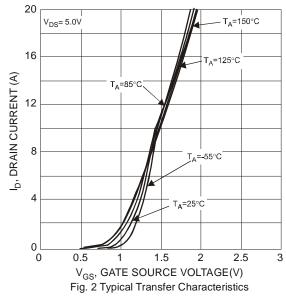
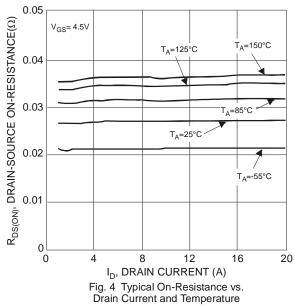
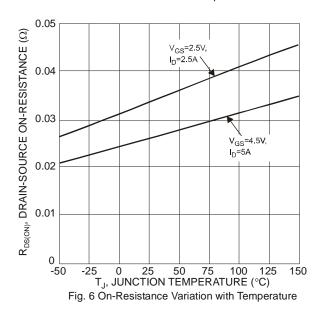


Fig. 3 Typical On-Resistance vs.











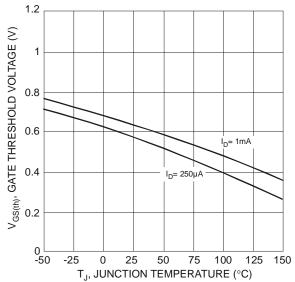
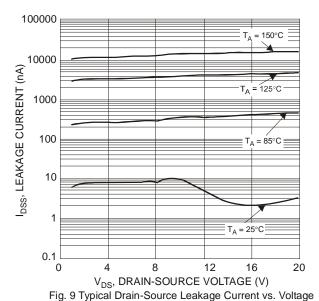


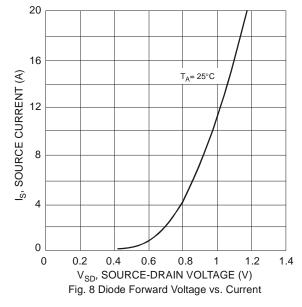
Fig. 7 Gate Threshold Variation vs. Ambient Temperature

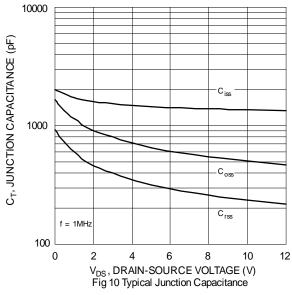


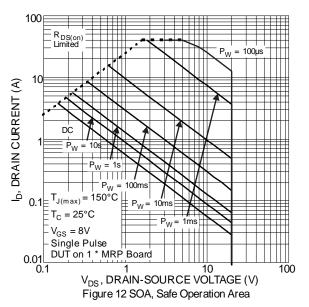
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V_{DS}=-10V, I_D=-4A

6
2
0
0
4
8
12
16
20
24
28

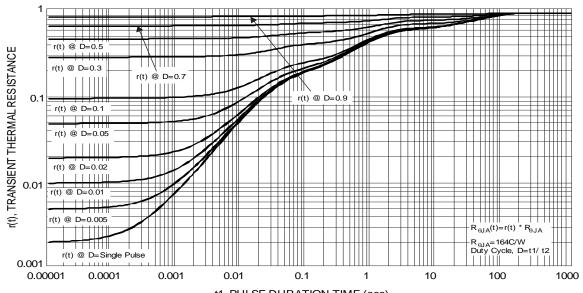
Fig. 11 Gate Charge Characteristics









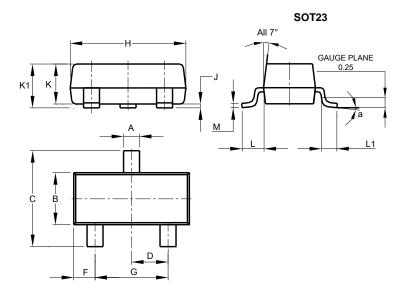


t1, PULSE DURATION TIME (sec) Fig. 13 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

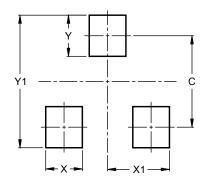


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K 1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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